

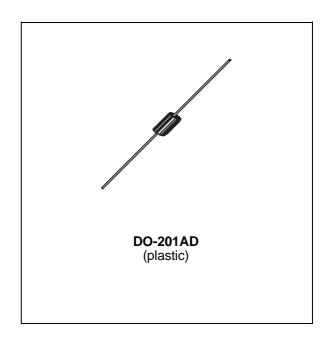
# HIGH VOLTAGE ULTRA-FAST DIODE FOR VIDEO

#### **MAJOR PRODUCT CHARACTERISTICS**

I <sub>Fpeak</sub>	4 A
V <sub>RRM</sub>	600 V
t <sub>rr</sub>	55 ns
V <sub>F</sub> (max)	1.2 V

#### **FEATURES AND BENEFITS**

- TURBOSWITCH<sup>™</sup> OUTSTANDING BENEFITS.
- HIGH REVERSE VOLTAGE: 600 V
- LOW POWER LOSSES INDUCING LOW TEMPERATURE AND HIGH RELIABILITY.
- OPTIMIZED TRADE-OFF BETWEEN t<sub>rr</sub> AND SOFTNESS FOR VIDEO HORIZONTAL DEFLECTION.



#### **DESCRIPTION**

High voltage ultra-fast diode especially designed for modulation and flyback rectification in standard and high resolution displays for TV's and monitors.

The device is packaged in a DO-201AD axial enveloppe.

### **ABSOLUTE RATINGS** (limiting values)

Symbol	Paramete	VALUE	Unit
VRRM	Repetitive peak reverse voltage	600	V
I <sub>F</sub> peak	Forward peak current (1)	4	А
I <sub>FRM</sub>	Repetitive peak forward current	100	А
I <sub>FSM</sub>	Surge non repetitive forward current	80	А
T <sub>stg</sub>	Storage temperature range	- 40 to 150	°C
Tj	Maximum operating junction to	150	°C

<sup>(1)</sup> on infinite heatsink with 10mm lead length

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## MDV04-600

### THERMAL RESISTANCES

Symbol	Parameter	Max.	Unit
R <sub>th(j-l)</sub>	Junction to lead	20	°C/W
R <sub>th(j-a)</sub>	Junction to ambient on printed circuit L lead = 10mm	75	°C/W

# STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Con	Тур.	Max.	Unit	
I <sub>R</sub> *	Reverse leakage current	V <sub>R</sub> = 480V	Tj = 25°C Tj = 125°C		50 0.75	μA mA
V <sub>F</sub> **	Forward voltage drop	I <sub>F</sub> = 4 A	Tj = 25℃ Tj = 125℃		1.28 1.20	V V

### **DYNAMIC ELECTRICAL CHARACTERISTICS**

**TURN-OFF SWITCHING** 

Symbol	Parameter	Test Conditions	Тур.	Max.	Unit
t <sub>rr</sub>	Reverse recovery time	$I_F = 0.5A$ $I_R = 1A$ Irr = 0.25A	55	75	ns
		$I_F = 100 \text{ mA}$ $I_R = 100 \text{ mA}$ $I_{rr} = 10 \text{mA}$	130		ns

# **DYNAMIC ELECTRICAL CHARACTERISTICS**

**TURN-ON SWITCHING** 

Sy	/mbol	Parameter	Test Conditions	Тур.	Max.	Unit
	t <sub>fr</sub>	Forward recovery time	$I_F = 4 A$ $dI_F/dt = 100 A/\mu s$		0.5	μs
,	V <sub>FP</sub>	Peak forward voltage	Measured at1.1 x V <sub>F</sub> max. Tj = 25℃		15	V

To evaluate the maximum conduction losses use the following equation :

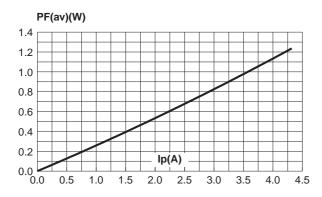
$$P = \frac{1.0 \ x \ l_p}{2} x \ \delta + \frac{0.050 \ x \ l_p^2}{3} \ x \ \delta$$

 $\boldsymbol{\delta}$  : duty cycle Ip: Peak current

Ex : for  $I_p = 4$  A and  $\delta = 0.5$ , P = 1.2 Watts.

Pulse test :  $^*$  tp = 5 ms,  $\delta$  < 2%  $^{**}$ tp = 380  $\mu$ s,  $\delta$  < 2%

Fig. 1: Power dissipation versus peak forward current (triangular waveform,  $\delta$ =0.5).



pad layout). K=[Zth(j-a)/Rth(j-a)]1E+0

Fig. 2: Relative variation of thermal impedance

junction to ambient versus pulse duration (epoxy printed circuit board, e(Cu)=35µm), recommended

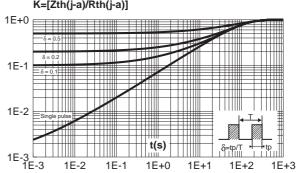
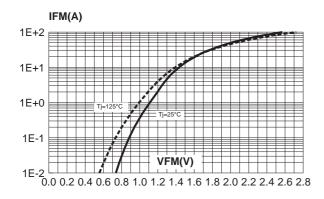


Fig. 3: Forward voltage drop versus forward current (maximum values).

Fig. 4: Reverse recovery time versus dIF/dt.



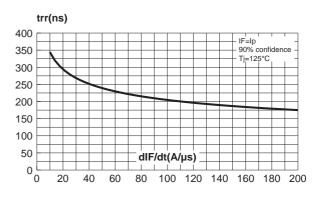
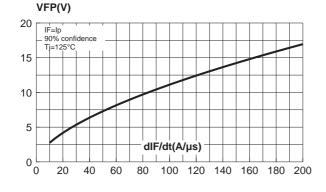
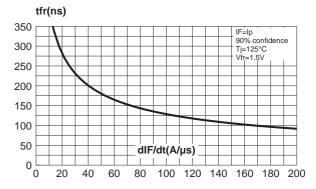


Fig. 5: Transient peak forward voltage versus dIF/dt.

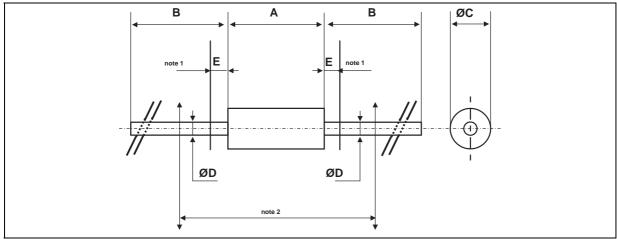
Fig. 6: Forward recovery time versus dIF/dt.





### **PACKAGE MECHANICAL DATA**

**DO-201AD** 



	DIMENSIONS					
REF.	Millim	neters	Inches		NOTES	
	Min.	Max.	Min.	Max.		
Α		9.50		0.374	1 - The lead diameter Ø D is not controlled over zone E	
В	25.40		1.000		2 - The minimum axial length within which the device may be	
ØC		5.30		0.209	placed with its leads bent at right angles is 0.59"(15 mm)	
ØD		1.30		0.051		
Е		1.25		0.049		

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
MDV04-600	MDV04-600	DO-201AD	1.166g.	600	Ammopack
MDV04-600RL	MDV04-600	DO-201AD	1.166g.	1900	Tape & reel

- Epoxy meets UL94,V0
- Polarity : Cathode indicated by polarity band

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